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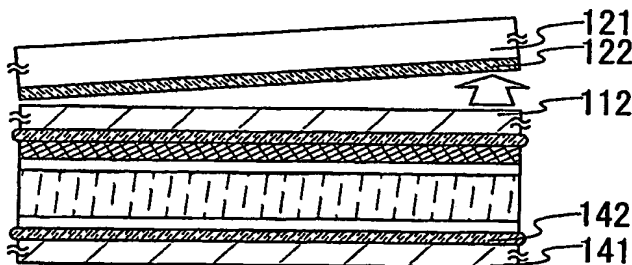
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(54) Title: METHOD OF MANUFACTURING DISPLAY DEVICE



(57) Abstract: To provide a method of manufacturing
a display device having an excellent impact resistance
property with high yield, in particular, a method of
manufacturing a display device having an optical film
that is formed using a plastic substrate. The method
of manufacturing a display device includes the steps
of: laminating a metal film, an oxide film, and an
optical filter on a first substrate; separating the optical
filter from the first substrate; attaching the optical
filter to a second substrate; forming a layer including
a pixel on a third substrate; and attaching the layer
including the pixel to the optical filter.

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